

# isc N-Channel MOSFET Transistor

## IXTP4N65X2

#### • FEATURES

- Static drain-source on-resistance:
   R<sub>DS</sub>(on) ≤ 850mΩ@V<sub>GS</sub>=10V
- Fully characterized avalanche voltage and current
- 100% Avalanche Tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



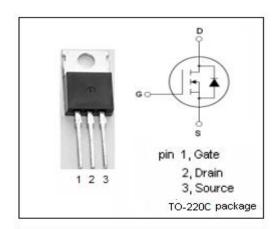
- · Switched mode power supplies
- DC-DC converters

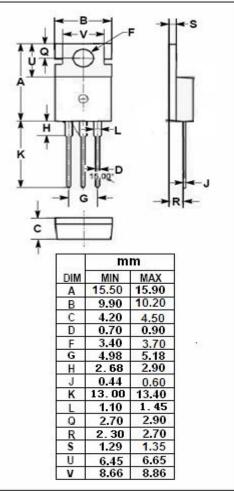
### • ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

PARAMETER	VALUE	UNIT	
Drain-Source Voltage	650	V	
Gate-Source Voltage	±30	V	
Drain Current-Continuous	4	А	
Drain Current-Single Pulsed	8	А	
Total Dissipation @T <sub>C</sub> =25°C	80	W	
Operating Junction Temperature	-55~150	$^{\circ}\!\mathbb{C}$	
Storage Temperature	-55~150	${}^{\mathbb{C}}$	
	Drain-Source Voltage  Gate-Source Voltage  Drain Current-Continuous  Drain Current-Single Pulsed  Total Dissipation @Tc=25°C  Operating Junction Temperature	Drain-Source Voltage $650$ Gate-Source Voltage $\pm 30$ Drain Current-Continuous       4         Drain Current-Single Pulsed       8         Total Dissipation @ $T_C=25^{\circ}C$ 80         Operating Junction Temperature       -55~150	

#### • THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R <sub>th(j-c)</sub>	Junction-to-case thermal resistance	1.56	°C/W







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#### **ELECTRICAL CHARACTERISTICS**

T<sub>C</sub>=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	МАХ	UNIT
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V; ID = 250 μ A	650		V
V <sub>GS(th)</sub>	Gate Threshold Voltage	V <sub>DS</sub> = V <sub>GS</sub> ; ID = 250 μ A	3.0	5.0	V
R <sub>DS(on)</sub>	Drain-Source On-Resistance	V <sub>GS</sub> =10V; I <sub>D</sub> = 2A		850	mΩ
I <sub>GSS</sub>	Gate-Source Leakage Current	V <sub>GS</sub> = ±30V;V <sub>DS</sub> =0V		±100	nA
I <sub>DSS</sub> Drain-Source Leakage	Drain Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V		5	μ <b>Α</b>
	Drain-Source Leakage Current	V <sub>DS</sub> = V <sub>DSS</sub> ; V <sub>GS</sub> = 0V;T <sub>J</sub> = 125°C		100	μА
V <sub>SD</sub>	Diode forward voltage	I <sub>F</sub> = 4A; V <sub>GS</sub> = 0V		1.4	V



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